

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--|------------------|---------|------------------|
| L2 | 289 | 438/142.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/04/10 10:30 |
| L3 | 399 | 438/421.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/04/10 10:30 |
| S45 | 1 | ((solid adj state) semiconductor metal gate) near (layer film material)) AND (((no near more) less) near "40" near Angstroms) AND (atomic\$4 near smooth near surface) AND ((metallurgical\$3 metal\$3) near bond\$3) AND (sufficient\$2 uniform\$2 (defect near free\$2)).CLM. | US-PGPUB; USPAT | OR | ON | 2005/11/04 08:24 |
| S46 | 1 | (method process\$3 fabricat\$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND (((no near more) less) near "40" near Angstroms) AND (atomic\$4 near smooth near surface) AND ((metallurgical\$3 metal\$3) near bond\$3) AND (sufficient\$2 uniform\$2 (defect near free\$2)).CLM. | US-PGPUB; USPAT | OR | ON | 2005/11/04 08:26 |
| S47 | 1 | (method process\$3 fabricat\$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND pocket AND (((no near more) less) near "40" near Angstroms) AND (atomic\$4 near smooth near surface) AND ((metallurgical\$3 metal\$3) near bond\$3) AND (sufficient\$2 uniform\$2 (defect near free\$2)).CLM. | US-PGPUB; USPAT | OR | ON | 2005/11/04 08:29 |
| S48 | 0 | (method process\$3 fabricat\$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND pocket AND (((no near more) less) near "40" near Angstroms) AND (atomic\$4 near smooth near surface) AND ((metallurgical\$3 metal\$3) near bond\$3) AND (sufficient\$2 uniform\$2 (defect near free\$2)) AND signal AND (interfac\$3 near rectify\$3 near barrier).CLM. | US-PGPUB; USPAT | OR | ON | 2005/11/04 08:28 |

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|-----|----|---|------------------------------|----|----|------------------|
| S49 | 1 | (method process\$3 fabricat\$3) AND (((solid adj state) semiconductor metal gate) near (layer film material)) AND pocket AND (((no near more) less) near (("0.1" near micron) ("40" near Angstroms))) AND (atomic\$4 near smooth near surface) AND ((metallurgical\$3 metal\$3) near bond\$3) AND (sufficient\$2 uniform\$2 (defect near free\$2)).CLM. | US-PGPUB; USPAT | OR | ON | 2005/11/04 08:36 |
| S57 | 50 | ("5225366" "5281274" "5668402" "4339300" "4825335" "4920076" "4999735" "5275687" "5627383" "5811319" "5842387" "5872016" "5989947" "6020247" "6150242" "6277681" "6365059" "6420729" "6599132" "6613677" "6893500" "6921726" "6930835" "6963137" "5244619" "5456798" "5496292" "6140617" "4856235" "5722945" "5911699" "6203518" "4245023" "4252473" "4301040" "4329394" "4395914" "4452669" "4587152" "4772060" "4786342" "4792381" "4889598" "4915511" "4919922" "4945325" "4967463" "5223093" "5471303" "5492528").pn. | US-PGPUB; USPAT; USOCR | OR | ON | 2006/04/04 10:36 |
| S58 | 62 | ("2788298" "2795742" "2813048" "2815304 "2890395" "2899343" "2973290" "301576 2" "3076104" "3081418" "3098160" "31002 76" "3124452" "3132057" "3142021" "3150 017" "3159780" "3192082" "3200311" "320 0468" "3209428" "3216871" "3226225" "32 26268" "3230609" "3233305" "3235779" "3 237062" "3247428" "3252062" "3255055"). PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2006/04/04 10:36 |